Contribution of weak localization to non local transport at norm alm etal / superconductor double interfaces

R.Melin

Centre de Recherches sur les Tres Basses Tem peratures, CRTBT*, CNRS, BP 166, 38042 Grenoble Cedex 9, France

In connection with a recent experiment [Russo et al., Phys. Rev. Lett. 95, 027002 (2005)], we investigate the e ect of weak localization on non local transport in norm almetal / insulator / superconductor / insulator / norm almetal (N ISIN) trilayers, with extended interfaces. The negative weak localization contribution to the crossed resistance can exceed in absolute value the positive elastic cotunneling contribution if the norm almetal phase coherence length or the energy are large enough.

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I. IN TRODUCTION

The manipulation of correlated pairs of electrons in solid state devices has aroused a considerable interest recently. The goals of this line of research are the realization of sources of entangled pairs of electrons for quantum inform ation, and the realization of fundam ental tests of quantum mechanics^{1,2}. Correlated pairs of electrons can be extracted from a superconductor by Andreev re ection, with extended or localized interfaces between superconductors and norm alm etals or ferrom agnets^{3,4,5,6,7,8,9}, and in Josephson junctions involving a double bridge between two superconductors¹⁰.

Charge is transported by Andreev re ection at a normalmetal/superconductor (NS) interface: an electron coming from the normal side is relected as a hole while a Cooperpair is transmitted in the superconductor¹¹. In the superconductor, Andreev re ection is mediated by an evanescent state of linear dim ension set by the superconducting coherence length . In structures in which a superconductor is multiply connected to norm alm etal electrodes separated by a distance of order ^{12,13}, the Andreev re ected hole in the spin-() band can be transmitted in an electrode di erent from the one in which the incoming spin- electron propagates. This \non local" transmission in the electron-hole channel is called \crossed Andreev re ection". Non local transmission in the electron-electron channel corresponds to \elastic cotunneling" by which an electron is transmitted from one electrode to another while spin is conserved 14 .

A schematic three-term inal device is represented on Fig. 1, as well as the voltages V_a and V_b applied on the norm all electrodes a" and b" respectively. The voltage V_s on the superconductor is chosen as the reference voltage ($V_s = 0$). Non local transport is characterized by a current I_a (V_b) circulating in electrode a" in response to a voltage V_b on electrode b". It is supposed in addition that $V_a = 0$: electrode a" is grounded, like in experiments^{8,9} (see Fig. 1). The crossed conductance is de ned by $G_{a,b}(V_b) = @I_a = @V_b(V_b)$. A crossed conductance dominated by elastic cotunneling (crossed Andreev relation) is negative (positive)¹⁵ because of the

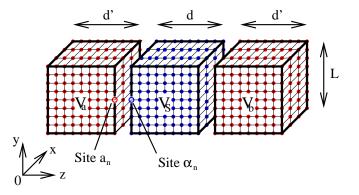


FIG.1: (Coloronline.) Schem atic representation of the tightbinding model of NISIN trilayer. The insulating layers are not shown on the gure. The aspect ratio is not to the scale of the experim ent in R ef. 9 for which d = 15; 50; 200 nm, L is of order of 5 m, and d^0 , 50 nm.

opposite charges of the outgoing particle in elastic cotunneling and crossed Andreev re ection. Lowest order perturbation theory in the tunnel amplitudes leads to $G_{a,b}\left(V_b\right) = 0$ because the crossed Andreev re ection and elastic cotunneling channels have in this case an exactly opposite contribution to the crossed conductance once the average over disorder^{16,17} or over the Ferm i oscillations in multichannel ballistic system $s^{14,18}$ is taken into account.

Three unexpected experimental features for the crossed conductance in a norm alm etal / insulator / superconductor / insulator / norm alm etal (N ISIN) trilayer have been reported recently by Russo et al^9 : i) The crossed conductance does not average to zero with normalm etals, in contradiction to the abovem entioned prediction of lowest order perturbation theory in the tunnel am plitudes¹⁴. The order ofm agnitude of the experimentally observed crossed signal is far from being compatible with low est order perturbation theory. ii) A magnetic eld applied parallel to the interfaces suppresses the non local signal, suggesting a phase coherent process. iii) The sign of the crossed resistance¹⁵ crosses over from positive (the sign of elastic cotunneling) to negative (the

sign of crossed Andreev re ection) as the bias voltage $V_{\rm b}$ increases, and the crossed signal disappears if the bias voltage exceeds the Thouless energy in the superconductor.

W e show here that weak localization with extended interfaces leads to a positive crossed conductance, the sign of which is opposite to the sign of the dom inant elastic cotunneling channel for localized interfaces¹⁹. The weak localization contribution to the crossed conductance becom es im portant at large bias voltages and for a large phase coherence length in the norm alm etals.

The article is organized as follows. Necessary preliminaries are given in Sec. II. The weak localization contribution to crossed transport is discussed in Sec. III. Concluding remarks are given in Sec. IV.

II. PRELIM INARIES

A. Ham iltonians

The norm alm etalelectrodes are described by the tight binding H am iltonian

$$H_{N} = \begin{pmatrix} X \\ k \end{pmatrix} c_{k;}^{\dagger} c_{k;} ; \qquad (1)$$

where k is the wave-vector, = ";# the projection of the electron spin on the spin quantization axis, and where

 $(k) = 2t_0 [\cos (k_x a_0) + \cos (k_y a_0) + \cos (k_z a_0)] is the dispersion relation of free electrons on a cubic lattice, with t_0 the bulk hoping am plitude, a_0 the distance between two neighboring sites, and k_x, k_y and k_z the projections of the electron wave-vector on the x, y and z axis (see Fig. 1).$

The superconductor is described by the BCS H am iltonian

$$H_{BCS} = \begin{cases} X & X \\ k_{k}; & k_{k}; \\ k_{k}; & k_{k} \end{cases} + \begin{cases} X & X \\ C_{k}^{\dagger}; C_{k}^{\dagger}; + C_{k}; \# C_{k}; \#$$

with the superconducting gap.

D iagonal disorder is included²⁰, with an elastic mean free path $l_e^{(N)}$ in the norm all electrodes of the N ISIN trilayer, and $l_e^{(S)}$ in the superconducting electrode. A – nite coherence length $l_e^{(N)}$ in the norm all electrodes is accounted for by adding phenom enologically an imaginary part to the energy.

At the extended interface a-, the tunnel H am iltonian connecting the electrodes $a^{"}$ and $h^{"}$ takes the form

$$\hat{W}_{a;} = \int_{n;}^{X} t c_{a_{n}}^{+}; c_{n}; + c_{n}^{+}; c_{a_{n}}; ; (3)$$

where the sites a_n on the norm alm etal side of the interface correspond to the sites $_n$ on the superconducting side of the interface (see Fig. 1), and a sim ilar expression holds for the tunnel H am iltonian at the interface b-.

B. Green's functions

The fully dressed advanced and retarded equilibrium N am bu G reen's function $\hat{G}^{A, R}$ (!) at energy ! is rst determ ined by solving the D yson equation

$$\hat{G}^{A,R}(!) = \hat{g}^{A,R}(!) + \hat{g}^{A,R}(!) - \hat{f}^{A,R}(!)$$
(4)

where denotes a sum mation over the spatial indices, and \hat{g}^{A} ^{;R} (!) are the advanced and retarded G reen's functions of the disconnected system (i. e. with t = 0 in the tunnel H am iltonian given by Eq. (3)). The self-energy \hat{t}_{t} corresponds to the couplings in the tunnel H am iltonian given by Eq. (3). The G reen's functions are 4 4 m atrices in the spin N am bu representation. The four com ponents correspond to a spin-up electron, a spin-down hole, a spin-down electron and a spin-up hole. Because of spin rotation invariance, some elements of the 4 4 G reen's functions are redundant. W e work here in a 2 2 block in the sector $S_z = -2$, encoding the superconducting correlations am ong a spin-up electron (N am bu label \1") and a spin-down hole (N am bu label \2").

O noe the fully dressed advanced and retarded G reen's functions have been obtained, the Keldysh G reen's function \hat{G}^+ ; is determined by the Dyson-Keldysh equation^{21,22,23,24,25}

$$\hat{G}^{+;} = \hat{I} + \hat{G}^{R} \stackrel{\uparrow}{} \hat{g}^{+;} \qquad \hat{I} + \stackrel{\uparrow}{} \hat{G}^{A}; (5)$$

where $\hat{g}^{\dagger i}$ is the K eldysh G reen's function of the isolated electrodes, and where the energy dependence of the G reen's functions is om itted.

C. Transport form ula

The current through the interface a- is given by

$$I_{a;} = \frac{2e}{h}^{Z} \frac{X \quad nh}{d!} \operatorname{Tr} f_{a_{n}; n} \hat{G}_{n;a_{n}}^{+} (!) \quad (6)$$

$$\stackrel{n}{f_{n;a_{n}}} \hat{G}_{a_{n}; n}^{+} (!) \stackrel{i}{\gamma_{3}} ;$$

where the trace is a sum m ation over the two components of the N am bu G reen's function, 3 is one of the Pauli m atrices, the diagonalelem ents of which are (1; 1), and the sum over n runs over all sites at the interface a-. As shown on Fig. 1, the symbols a_n and $_n$ in Eq. (6) label two corresponding sites at the interface, in the norm alelectrode \a" and in the superconductor respectively. The two spin orientations are taken into account in the prefactor of Eq. (6).

The local conductance of a N IN interface is equal to $(e^2=h)T$ per channel, where $T = 2 \frac{2}{L}t^2 \frac{2}{N}$ is the dimensionless transm ission coe cient in the tunnel limit, with N the norm aldensity of states²¹.

The non perturbative transport formula for the bcalcurrent at a localized N IN interface was obtained in

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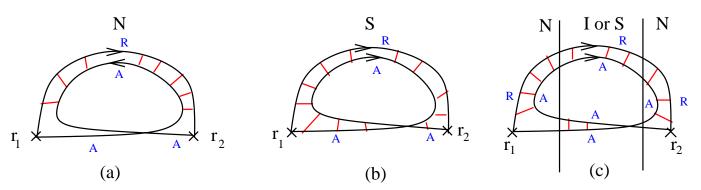


FIG. 2: (C obronline.) A weak localization diagram in a normal metal for which r_1 and r_2 are within the elastic mean free path l_e (a), and in a superconductor for which r_1 and r_2 are within . (c) represents the same diagram at a N ISIN double interface, equivalent to Fig. 3c. In the N ISIN case on (c) r_1 and r_2 are within and r_1 , r_2 are within $l_e^{(N)}$ from the interfaces. In the N IN case on (c), r_1 and r_2 are within the insulator correlation length. (A " and (R " stand for advanced and retarded.

Ref. 21, and generalized in Ref. 25 to a localized N IS interface, and in Ref. 19 to non local transport at a double ferrom agnet / superconductor interface. We deduce from these references the exact expressions of the local conductance $G_{N IN}$ (V) of a single N IN interface, of the Andreev conductance $G_{N IS}$ (V) of a single N IS interface, and of the crossed conductance $G_{a,b}$ (V_b) of a N ISIN trilayer with extended interfaces:

$$G_{N IN} (V) = 8 \frac{2}{h} \frac{e^2}{h} t^4$$

$$X \frac{1}{\sum_{\substack{a_1, a_3 \\ a_1, a_3}} G_{j;k}^{A;1;1} (eV) \sum_{\substack{b_k, b_1 \\ b_k, b_1}} G_{j;k}^{R;1;1} (eV)}$$

$$G_{N IS} (V) = 16 \frac{2}{h} \frac{e^2}{h} t^4$$

$$X \frac{1}{\sum_{\substack{a_1, a_3 \\ a_1, a_3}} G_{j;k}^{A;1;2} (eV) \sum_{\substack{b_k, b_1 \\ b_k, b_1}} G_{j;k}^{R;2;1} (eV)}$$
(8)

j**;**k**;**l

$$G_{a,b}(V_{b}) = \frac{8 \frac{2}{h} e^{2}}{1} t^{4}$$
(9)
$$X \frac{n}{\text{Tr} \frac{N}{a_{i}; a_{j}}^{N} (3G^{A})_{j; k}} (eV_{b}) \frac{N}{b_{k}; b_{1}}^{N} (3G^{R})_{j; i}} (eV_{b})^{0};$$

valid to all orders in the hopping am plitude. The crossed conductance $G_{a,b}$ (V_b) is per conduction channel through the junction of area L L, with a superconducting layer of thickness d (see Fig. 1). The sum mations in Eqs. (8) and (9) run over all pairs of sites at the interfaces, and the overline denotes disorder averaging. The density of states $\stackrel{N}{a_{i};a_{j}} = (\hat{g}^{A}_{a_{i};a_{j}} \quad \hat{g}^{R}_{a_{i};a_{j}})=2i$ connects the sites a_{i} and a_{j} in electrode \a", and a similar de nition holds for \sum_{b_i, b_i}^{N} . The site a_j (b₁) in electrode \a" (\b") is connected by the tunnel H am iltonian to the site $\frac{1}{1}$ (1) in the superconductor (see Fig. 3 for the N ISIN interface). In the case of the local conductance of a N IN junction, $_{i}$, $_{k}$, $_{1}$ and $_{i}$ belong to an insulating layer that has been inserted in between the two normalmetals. The tunnel am plitude t in Eq. (7) connects in this case the norm alm etalto the insulator, while t in Eqs. (8) and (9) connects the norm alm etal to the superconductor.

The fully dressed advanced and retarded equilibrium N am bu G reen's functions $\hat{G}_{j,k}^{A}$ (!) and $\hat{G}_{1,j}^{R}$ (!) at energy ! in Eqs. (7), (8) and (9) are expanded by using the D yson equation given by Eq. (5). We deduce from the exact K eldysh transport form ula given by Eqs. (7), (8) and (9) that the diagram s are connected, and that the propagators for the density of states are directly connected to at least one tunneling vertex. The other extrem ity of the density of states propagators is connected either to a tunneling vertex, or to a disorder scattering vertex. The density of states, represented by wavy lines on the diagram s, connects to one advanced and one retarded G reen's function as in Eqs. (7), (8) and (9).

A crossed conductance dom inated by elastic cotunneling (crossed Andreev re ection) is negative (positive)¹⁵. This can be seen m ost sim ply by m aking the N am bu labels explicit in Eq. (9) and taking into account the signs in the 3 m atrices, and the global sign.

The crossed conductance is expanded perturbatively in T 2 , where the norm allocal transm ission coe cient T has already been de ned, and is also expanded in the num ber of non local processes crossing the superconductor since d & 14 .

D. W eak localization in a superconductor

W eak localization in a superconductor was already investigated in Ref. 26 in connection with the determ ination of the number density of superconducting electrons. A weak localization diagram in a bulk normal metal is shown on Fig. 2a. In this case the two points r_1 and r_2 are within the elastic mean free path $l_e^{(N)}$. In a bulk superconductor (see Fig. 2b), the two points r_1 and r_2 are within the coherence length since the disorder average g^A ; g^A ; of two advanced G reen's functions between the two sites and at r_1 and r_2 in a superconductor is limited by , not by $\frac{1}{2}$. Sim ilar diagram s for the conductance are introduced at a NISIN double interface in Sec. III. In this case the points r_1 and r_2 are separated

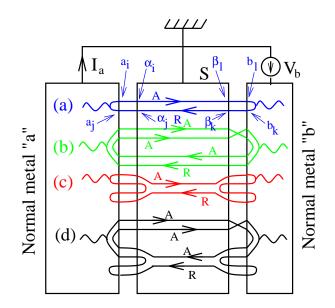


FIG.3: (Color online.) The lowest order diagram s contributing to crossed transport. We show (a) the vanishing diagram of order T^2 , (b) the vanishing weak localization diagram of order T^4 , (c) the rst non vanishing diagram of order T^4 , and (d) the weak localization diagram of order T^6 . The wavy lines correspond to the insertion of the norm almetal density of states, and of a 3 m atrix.

by the superconductor thickness, of order (see F ig. 2c). At a N IN interface, the two points r_1 and r_2 on di erent interfaces can be separated by a distance equal to the thickness of the insulator, comparable to the decay length induced by the charge gap of the insulator.

III. NON LOCAL TRANSPORT IN A NISIN TRILAYER

A . C rossed conductance to order $T^{\,2}$

Now we evaluate the lowest order diagram s appearing in the crossed conductance of a N ISIN trilayer. The crossed conductance due to the diagram of order T² (see Fig. 3a) vanishes because the contributions of the elastic cotunneling and crossed Andreev re ection channels are exactly opposite^{14,16,18,19}. This can be seen also by evaluating the sum mation over the N am bu labels in the diagram on Fig.3 and using $\overline{g_{;i}^{1;1}g_{;i}^{1;1}} = \overline{g_{;i}^{1;2}g_{;i}^{2;1}}$, where and are two points in the superconductor at a distance of order .

B. Crossed conductance to order T 4

The rst weak localization diagram of order T⁴ involving four G reen's functions in the superconductor is shown on Fig. 3b. The corresponding crossed conductance vanishes, as for the diagram of order T² discussed in Sec.IIIA.

The diagram of order T⁴ on Fig. 3c takes a nite value, and is evaluated explicitly by sum ming over all possible Nam bu labels, and over the di erent possibilities of inserting the density of states and the 3 m atrices (represented by the wavy lines on the diagram s). This leads to the crossed conductance

$$G_{a,b}(V_{b}) = 4^{2} t^{8} {}^{6}_{N} X \overline{g^{1;1;A}(eV_{b})g^{2;2;R}(eV_{b})} (10)$$

$$\overline{g^{1;2;A}(eV_{b})g^{1;2;R}(eV_{b})} \frac{2^{2}}{2^{2}(eV_{b})^{2}};$$

where¹⁹

$$\overline{g_{j}^{1,1}(!)g_{j}^{2,2}(!)} = \frac{2}{2} \frac{2}{s} (R) \exp \left(\frac{2R}{(!)} \frac{2!^{2}}{2} \frac{2}{2}\right)$$
$$\overline{g_{j}^{1,2}(!)g_{j}^{1,2}(!)} = \frac{2}{2} \frac{2}{s} (R) \exp \left(\frac{2R}{(!)} \frac{2}{2} \frac{2}{2}\right)$$

with R the distance between the sites and , and with (R) = $(k_{\rm F} R)^2$ in the ballistic limit, and (R) = $k_{\rm F}^2 R l_{\rm e}^{\rm (S)}$ in the di usive limit. The resulting term of order T⁴ in the crossed conductance is given by

$$G_{a,b}^{(ec)}(V_b) = -\frac{e^2}{h}T^4 \frac{2}{l_e^{(S)}} \frac{2}{2} (eV_b)^2 \exp - \frac{2d}{2} ;$$
(11)

in agreement with the expansion to order T⁴ of the crossed conductance obtained for highly transparent localized interfaces¹⁹. A summation over the pairs of sites and at the two interfaces was carried out, giving rise

to the prefactor $=l^{(S)}$ in Eq. (11).

C. W eak localization diagram of order T⁶

1. Contribution of local excursions

We consider now the weak localization diagram of order T⁶ on Fig. 3d, merging the features of the two diagrams of order T⁴ on Figs. 3b and c, and shown in more details on Fig. 4. The long range propagation in the normal electrodes involves the di usons $\overline{g_{i}^{A;1;1}g_{i}^{R;1;1}}$ and $\overline{g_{i}^{A;2;2}g_{i}^{R;2;2}}$ in the particle particle or hole-hole channel (where and belong to the normal electrode), as opposed to the di uson $\overline{g_{i}^{A;1;1}g_{i}^{A;2;2}}$ in the particlehole channel for local Andreev rejection at a single N IS interface^{27,28} below the related Thouless energy.

We rst evaluate the part of the diagram on Fig. 4 involving local excursions at the N IS interfaces (see Fig. 5). Enumerating these diagrams shows that the two local excursions are attached to the same non local propagation in the superconductor. We use the notation $X_{;00}^{A;R}$ ($X_{;00}^{A;R}$) for the part of the diagram on Fig. 5 with two advanced (one advanced and one retarded) propagators

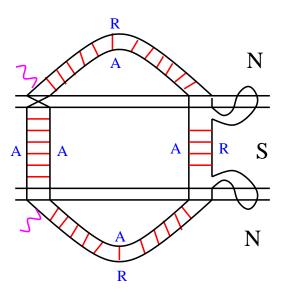


FIG. 4: (Color online.) Details of the insertion of the densities of states and of the 3 m atrices in the weak localization diagram on Fig. 3d. \A" and \R" stand for advanced and retarded. The di usons are calculated in the ladder approximation. The rungs of the ladders represented by the red lines represent schem atically the di uson in the ladder approximation.

in the superconductor, and the N am bu labels (;) and ($^{\rm 0};$ $^{\rm 0})$ at the extrem ities in the two norm al electrodes. We nd

$$X_{11;11}^{A;A} = X_{11;22}^{A;A} = \frac{8 {}^{2} {}^{6}_{N}}{(R)} \frac{!^{2} {}^{2}}{({}^{2} {}^{2} {}^{2})^{2}}$$
 (12)

$$X_{11;11}^{A;R} = X_{11;22}^{A;R} = \frac{2 {}^{2} {}^{6}_{N}}{(R)} - \frac{2}{2 {}^{2} {}^{12}}$$
(13)

We recover Eq. (11) for the non vanishing diagram of order T⁴ on Fig. 3c, proportional to $(X_{11,11}^{A,R}, X_{11,22}^{A,R})$. The globalm inus sign in this expression can be found in Eq. (9), and the opposite signs for $X_{11,11}^{A,R}$ and $X_{11,22}^{A,R}$ are due to the matrices 3 in Eq. (9). The diagram s with local excursions attached to the disorder average of two advanced or two retarded G reen's functions in the superconductor lead to a vanishingly sm all crossed conductance, as it can be seen from the identity $(X_{11,11}^{A,R}, X_{11,22}^{A,R}) = 0$, deduced from Eq. (12).

D. W eak localization crossed conductance

The weak localization contribution to the crossed conductance corresponding to the diagram on Fig. 4 is given by

$$G_{a;b}^{(w \ l)}(eV_{b}) = G_{a;b}^{(ec)}(V_{b})F - \frac{d}{r}; \frac{V_{b}}{L_{e}^{(N)}}; \frac{L^{(N)}}{L_{e}^{(N)}}; \quad (14)$$

where $G_{a,b}^{(ec)}$ (V_b) is given by Eq. (11) and

$$F = \frac{d}{l}; \frac{V_{b}}{l}; \frac{L^{(N)}}{L^{(N)}} =$$
(15)

$$\frac{1}{4}T^{2} \quad \frac{\underline{l}^{(N_{1})}}{\underline{l}^{(N_{1})}_{e}} \quad \frac{1}{\underline{l}^{(S_{1})}_{e}} \quad \frac{2}{2} \quad (eV_{b})^{2} exp \qquad \frac{2d}{2} \quad :$$

The sign of $G_{a,b}^{(w\ l)}$ (eV_b) given by Eq. (14) is positive, as for crossed Andreev rejection. The factor $(L^{(N)} = l_e^{(N)})^4$ is due to a a factor $(L^{(N)} = l_e^{(N)})^2$ associated to the di usons in each of the quasi-two-dimensional norm allayers [see Eq. (A 5)] in the limit q = 0. The constraint q = 0 originates from the conservation of the component of the wave-vector parallel to the interface, due to the symmetry by translation parallel to the interfaces (see Appendix B).

It can be shown that the two diagrams of order T 6 involving a single di uson in the superconductor and long range propagation in the normal metals are negligible because of the sum over the Nambu labels in one diagram, and because of the factor $(l_{\ell}^{(N)}=l_{e}^{(N)})^2$ in the other diagram, much smaller than $(l_{\ell}^{(N)}=l_{e}^{(N)})^4$ for the weak localization diagram.

The weak localization crossed conductance can be expanded system atically in powers of (L = $L_e^{(N-)}$)²:

$$G_{a,b}(eV_b = 0) = \frac{e^2}{h} X_n A_n (T) \frac{1}{l_e^{(N)}}^{2n} :$$
 (16)

The coe cients A $_{\rm n}$ (T) are evaluated to leading order in T because of the sm all interface transparencies. Estim ating the higher order weak localization diagrams leads to A₃ T⁸, A₄ = 0, A₅ T¹⁰, A₆ = 0, A₇ T¹², ... The order of magnitude of the sum of the higher order contributions can be obtained from summing the corresponding geometric series for T ($L = l_e^{(N)}$)² > 1: P ______ A_n(T) L = l_e^{(N)} is of order T² L = $l_e^{(N)}$ ⁴, much sm aller than A₂(T) L = $l_e^{(N)}$ ⁴, therefore justifying why we based our discussion on the rst two terms A₀(T) T⁴ and A₂(T) T⁶.

E. Relation to experim ents

1. Determ ination of the parameters

The number of channels N_{ch} for a contact with a threedimensional metal is N_{ch} = S = $_{\rm F}^2$, where S is the junction area and _F the Ferm i wave-length. The normal layers have a dimension L L d⁰, with L' 5 m and a thickness d⁰ ' 50 nm (see Fig. 1). The number of channels in the quasi-two-dimensional geometry is obtained be neglecting disorder (the elastic mean free path in the experiment is limited by scattering on the normal lm

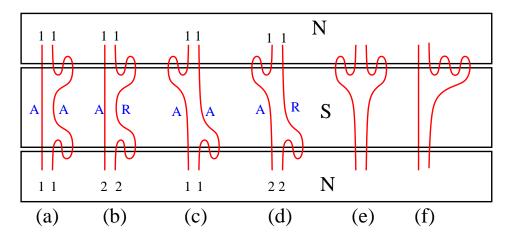


FIG.5: (Color online.) Representation of the part of the diagram of order T^6 (see Fig.3) with local excursions. $1^{"}$ and $2^"$ correspond to the Nam bu labels. (a), (b), (c) and (d) contribute respectively to $X_{11,11}^{A,R}$, $X_{11,22}^{A,R}$, $X_{11,11}^{A,R}$ and $X_{11,22}^{A,R}$. The diagram s having the topology of (e) and (f) lead to a vanishingly sm all crossed conductance because of the matrices 3 and the trace over the Nam bu labels.

boundaries), and by evaluating the area of the Ferm i surface with discrete wave-vectors in the direction perpendicular to the interface, leading to N $_{\rm ch}$ = Ld⁰= $_{\rm F}^2$ ' 6 10⁵. The norm altransparency T can be obtained from the local conductance in the norm al state R $_{\rm N}^{\rm (loc)}$ ' 2 :

$$\frac{1}{R_{\rm N}^{\rm (loc)}}$$
 ' 2N_{ch}T $\frac{e^2}{h}$; (17)

leading to T ' 10 ². These values T ' 10 ² and N _{ch} ' 6 10⁵ are compatible with the local Andreev resistance at zero bias of about 100 , being an upper bound to the zero temperature Andreev resistance R ^(loc)_A given by 1=R ^(loc)_A = 2 (e²=h)T ²N _{ch}. Russo et al.⁹ estimate T ' 10 ⁵ from N _{ch} = S = ²_F for a three dimensional metal. The possible dependence of N _{ch} on d⁰ that we consider here can be probed experimentally by determining how the crossed resistance depends on the thickness of the norm al layers.

2. Crossed resistance

The crossed resistance matrix measured experimentally⁹ is the inverse of the crossed conductance matrix. The o-diagonal element of the crossed resistance matrix is given by

$$R_{a,b}^{(tot)}(V_{b}) = \frac{G_{a,b}^{(tot)}(V_{b})}{G_{a,a}^{(tot)}(V_{b})G_{b,b}^{(tot)}(V_{b}) - G_{a,b}^{(tot)}(V_{b})G_{b,a}^{(tot)}(V_{b})};$$
(18)

where $G_{a;a}^{(tot)}(V_b) = G_{b;b}^{(tot)}(V_b) = G_{bc}^{(tot)}(V_b)$ is the local Andreev conductance.

The elastic cotunneling crossed resistance correspond-

ing solely to the contribution of Eq. (11) is thus of order

$$R_{a;b}^{(ec)}(V_{b} = 0) = \frac{1}{4N_{ch}} \frac{h}{e^{2}} \frac{1}{l_{e}^{(S)}}$$
$$\frac{\frac{2}{(eV_{b})^{2}}}{2} \exp(2d=); (19)$$

having an order of magnitude compatible with the experiment⁹. The elastic cotunneling crossed resistance is independent on T for tunnel interfaces. The elastic cotunneling crossed resistance R $_{a,b}^{(ec)}$ ($V_b = 0$) being inversely proportional to N $_{ch}$, with N $_{ch}$ proportional to d⁰ (see Sec. IIIE 1), it is expected that the crossed resistance would decrease if the norm alm etal layer thickness d⁰ increases, as anticipated in Sec. IIIE 1.

 $\ensuremath{\operatorname{N}}\xspace$ we were associated to

$$R_{a;b}^{(w l)} = R_{a;b}^{(ec)} F - \frac{d}{r}; \frac{V_b}{r}; \frac{L^{(N)}}{L_{a}^{(N)}} : \qquad (20)$$

The voltage dependence of the total crossed resistance R_{a,b}(V_b) = R_{a,b}^(ec)(V_b) + R_{a,b}^(W l)(V_b) is shown on Fig. 6 for di erent values of $L^{(N)} = l_e^{(N)}$. We obtain a change of sign from a positive (elastic cotunneling dom inated) to a negative (weak localization dom inated) crossed resistance as the voltage increases (see Fig. 6). For sufciently large values of the phase coherence length, we have F d= ;0; $l^{(N)} = l_e^{(N)} > 1$ as discussed above, so that the crossed resistance is negative for all values of the bias voltage.

The perturbative crossed resistance on Fig.6 tends to a nite value in the limit $eV_{\rm b}$ = . The determ ination of the crossed conductance around $eV_{\rm b}$ = \$ is exam ined in Ref. 19 for localized interfaces with arbitrary interface transparencies. The non perturbative crossed conductance tends to zero for $eV_{\rm b}$ = \$, but the cross-over

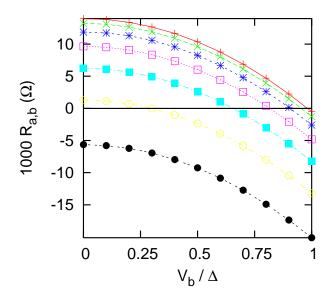


FIG. 6: (Color online.) Voltage dependence of the crossed resistance (in 0 hm s), given by Eq. (18), in which the crossed conductance is the sum of the elastic cotunneling [see Eq. (11)] and weak localization [see Eq. (14)] contributions. We used the parameters d = 20 nm, = 15 nm, $l_{e}^{(N)} = 50 \text{ nm}$, $l_{e}^{(S)} = 3 \text{ nm}$, $T = 10^{-2}$, $N_{ch} = 6 = 10^{5}$. The values of $l_{e}^{(N)}$ are, from top to bottom: $l_{e}^{(N)} = 0.4$; 0.5; 0.6; 0:7; 0.8; 0:9; 1 m. The points are theoretical, and the lines are a guide to the eye.

occurs within an energy window that becomes very small for tunnel interfaces. A crossed current related to out-of-equilibrium quasiparticle populations (not described here) is expected for $eV_{\rm b}>$.

A sit is visible on F ig. 6, the characteristic voltage scale in the bias voltage dependence of the crossed resistance is the superconducting gap, not the norm al state superconductor T houless energy obtained in experim ents. At the present stage, we do not nd a plausible explanation of this experim ental observation.

F. Magnetic eld dependence

The experimental crossed signal is suppressed by a magnetic eld parallel to the layers⁹. The theoretical weak localization crossed signal is also suppressed by a magnetic eld because the corresponding diagram dephases in an applied magnetic eld. The cross-overm agnetic eld B for the suppression of the weak localization crossed conductance corresponds to one superconducting ux quantum $_0$ enclosed in the area of the diagram, com patible with experiments⁹. How ever, in experiments, the crossed resistance is suppressed by a magnetic eld in the entire voltage range. The present model does not explain the dephasing of the elastic cotunneling contribution.

IV. CONCLUSIONS

We have calculated the weak localization contribution to non local transport in N ISIN trilayers with extended interfaces and a su cient phase coherence length in the norm alelectrodes. We nd a change of sign in the crossed resistance between elastic cotunneling at low voltages and weak localization at higher voltages. The weak localization contribution can dom inate for all voltages if the phase coherence length is large enough. The weak localization crossed conductance dephases in an applied m agnetic eld, but not the elastic cotunneling contribution. The appearance of a voltage scale related to the superconductor Thouless energy is left as an important open question.

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APPENDIX A:DIFFUSION PROBABILITIES IN A NORMALMETAL

1. Diusion in the electron-electron channel

We rst discuss brie y the norm alm etaldi uson in the ladder approximation. In the Born approximation, the elastic scattering time $_{1;1}$ in the \11" G reen's function given by

$$g_{1;1}^{A;R}$$
 (k;!) = $\frac{1}{!}$ (A1)

is de ned by k_F^3 $_{1,1}v^2 = (4 _F) = 1$, with $_{1,1} = _0 [1 + ! = (2 _F)]$, where $_0$ is the elastic scattering time at the Ferm i level, v is the amplitude of the m icroscopic im - purity scattering potential, k_F is the Ferm i wave-vector, and $_F$ the Ferm i energy.

U sing contour integration, and the identity

^Z
$$\frac{dk}{(2)^{3}}f(k) = \frac{1}{8^{2}} \int_{1}^{Z_{+1}} k^{2} dk \int_{1}^{Z_{1}} duf(k;u)e^{ikRu};$$

(A2)

with $k = \frac{1}{2} jand f(k)$ a function of k, we obtain easily

$$\frac{Z}{\frac{dk}{(2)^{3}}} g_{N}^{1;1} (k) g_{N}^{1;1} (k+q) \qquad (A 3)$$

$$\frac{k_{F}^{3}}{4} \frac{1;1}{F} = 1 - \frac{D_{0}}{4} q_{1}^{2} + (L^{(N)})^{2} \frac{1}{2};$$

where D is the di usion constant. The Fourier transform $P^{N}(q)$ of the di usion probability $P^{N}(r)$, given by

$$P^{N}(q) = t_{0}^{2} \frac{dk}{(2 - a_{0})^{3}} \overline{G_{1;1}^{R}(k; !)G_{1;1}^{R}(k + q; !)}; \quad (A 4)$$

where the overline is a disorder averaging and t_0 is the bulk hopping integral (see Eq. (1)), is obtained by sum – m ing the ladder series, leading to

$$P^{N}(q) = \frac{4}{D_{0}} \frac{1}{q^{2} + (\underline{\mu}^{(N)})^{2}} : \qquad (A5)$$

In this expression P^{N} (q) has no dimension. Its Fourier transform P^{N} (R) is such that P^{N} (R) dR has no dimension, as expected for a probability.

APPENDIX B:DOUBLE NS INTERFACE

W e provide now explanations to the factor $(\mathbf{L}^{(N)} = \mathbf{l}_{e}^{(N)})^{4}$ appearing in Eq. (15) for quasi-two-dimensional normal electrodes. Because of the conservation of the component of the wave-vector parallel to the interface at each tunneling vertex, and because of the form of the diagram, the diagram on Fig. 4 is evaluated at $q_k = 0$, where q_k is the projection of q (see Appendix A) on a plane parallel to the interfaces. By momentum conservation, a nite value of q_k is transformed in q_k after traversing the entire diagram, so that $q_k = q_k = 0$. The resulting crossed conductance is thus proportional to P^{N} (q_k = 0)², where the square is due to the correlated di usion in the two norm al electrodes, and where the diusion probability P $^{\rm N}$ (q_k) is given by Eq. (A 5). $(l_{2}^{(N)} = l_{2}^{(N)})^{4}$ since the norm al This lead to the factor

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m etals are quasi-two-dimensional so that $q_2 = 0$, where q_2 is the projection of q on the normal to the interfaces.

APPENDIX C:BALLISTIC NISIN TRILAYER W ITH ATOM IC THICKNESS

We consider in this Appendix a ballistic N IS IN trilayer with atom ic thickness^{29,30} in which the three electrodes are two-dimensional, and nd a factor $(l_{\ell}^{(N)} = l_{e}^{(N)})^{3}$, sim - ilar to the factor $(l_{\ell}^{(N)} = l_{e}^{(N)})^{4}$ factor discussed previously in the di usive lim it.

The transport formula given by Eq. (9) is Fourier transform ed, to obtain

$$G_{a,b}(V_{b}) = 8 \frac{2}{h} e^{\frac{2}{h}} t^{4} \frac{d^{2}k}{(2)^{2}}$$
(C1)
n
Tr $\bigwedge_{a,a}^{N}(k) \bigwedge_{3} \hat{G}^{A}$; $(k; eV_{b}) \bigwedge_{b,b}^{N} \bigwedge_{3} \hat{G}^{R}$; $(k; eV_{b})$;

and the Dyson equations for $\hat{G}^{A,R}$ (k) are also Fourier transform ed. The norm all metal ballistic G reen's function is given by $g_{a,a}^{1,1}$ (k;!) = 1=[! + i], where is the kinetic energy with respect to the Ferm i level, and where the broadening parameter is given by = $\sim_{\Psi} \mathbb{1}^{(N)}$. Eq. (C1) is then expanded diagram matically. A diagram similar to the one on Fig. 4 leads to a factor $^{3} = (\sim_{V_{T}} \mathbb{1}^{(N)})^{3}$.

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